

**isc Silicon NPN Power Transistor**
**2SC4764**
**DESCRIPTION**

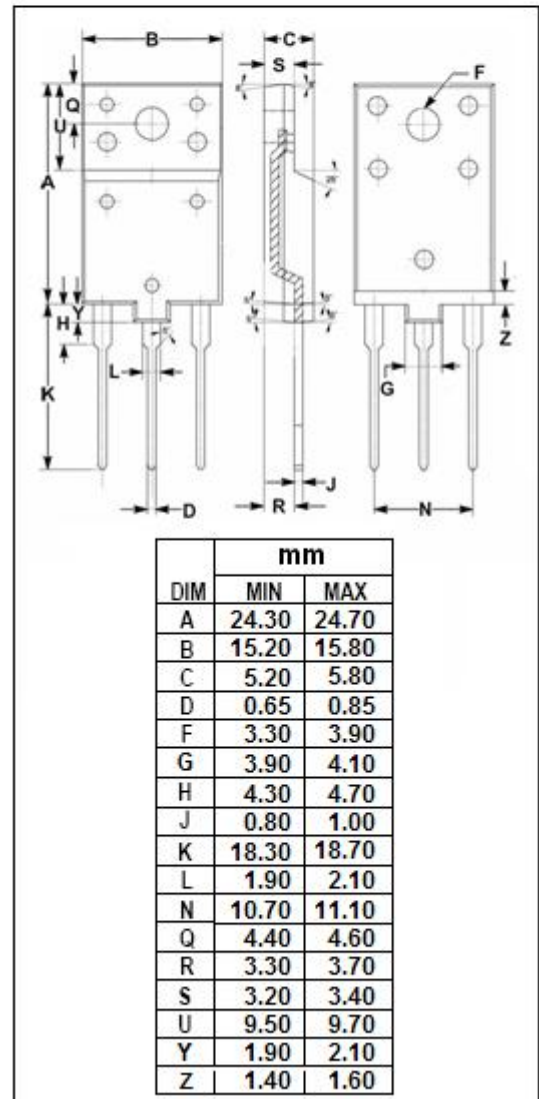
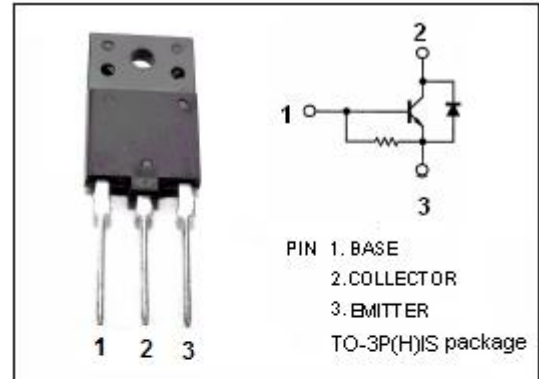
- High Breakdown Voltage-  
:  $V_{CBO} = 1500V$  (Min)
- High Switching Speed
- Low Saturation Voltage
- Built-in Damper Diode
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Horizontal deflection output for medium resolution display.

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	600	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current- Continuous	$\pm 6$	A
$I_{CP}$	Collector Current-Pulse	$\pm 12$	A
$I_B$	Base Current- Continuous	3	A
$P_C$	Collector Power Dissipation @ $T_c = 25^\circ C$	50	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



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**ELECTRICAL CHARACTERISTICS**

 T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 300mA ; I <sub>C</sub> = 0	5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.8A			5.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.8A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 1500V ; I <sub>E</sub> = 0			1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V ; I <sub>C</sub> = 0	83		250	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 5V	8			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A ; V <sub>CE</sub> = 5V	5		9	
V <sub>ECF</sub>	C-E Diode Forward Voltage	I <sub>F</sub> = 4A			1.8	V
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A ; V <sub>CE</sub> = 10V	1	3		MHz
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> = 10V;f <sub>test</sub> =1.0MHz		170		pF

Switching times ;Resistive load

t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 4A , I <sub>B1</sub> = 0.8A ; I <sub>B2</sub> = -1.6A R <sub>L</sub> = 51 Ω			2.5	μ s
t <sub>f</sub>	Fall Time				0.2	μ s

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